



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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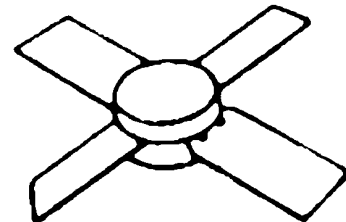


MS2341

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

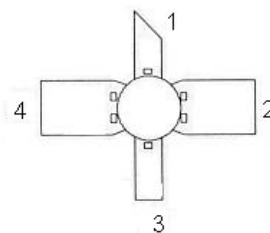
Features

- DESIGNED FOR HIGH POWER PULSED IFF, DME, AND TACAN APPLICATIONS
- 40 W (typ.) IFF 1030–1090 MHz
- 35 W (min.) DME 1025–1150 MHz
- 25 W (typ.) TACAN 960–1215 MHz
- 960 - 1215 MHz
- GOLD METALLIZATION
- Pout = 25 W MINIMUM
- Gp = 9.0 dB
- INTERNAL INPUT MATCHING
- INFINITE VSWR CAPABILITY @ RATED CONDITIONS
- COMMON BASE CONFIGURATION



**.280 4LSL (M115)
epoxy sealed**

PIN CONNECTION



1. COLLECTOR 3. EMITTER
2. BASE 4. BASE

DESCRIPTION:

The MS2341 is a gold metallized silicon, NPN power transistor designed for applications requiring high peak power and low duty cycles such as IFF, DME, and TACAN. The MS2341 utilizes internal impedance matching for improved broadband performance.

ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	65	V
V _{CES}	Collector-Emitter Voltage	65	V
V _{EBO}	Emitter-Base Voltage	3.5	V
I _C	Device Current	2.6	A
P _{DISS}	Power Dissipation	87.5	W
T _J	Junction Temperature	200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)}	Junction-case Thermal Resistance	2.0	°C/W
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ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)
STATIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV_{CBO}	I_C = 20 mA I_E = 0 mA	60	---	---	V
BV_{CES}	I_C = 20 mA V_{BE} = 0 V	60	---	---	V
BV_{EBO}	I_E = 2.0 mA I_C = 0 mA	3.5	---	---	V
I_{CBO}	V_{CB} = 50 V I_E = 0 mA	---	---	2	mA

DYNAMIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
P_{OUT}	f = 1025 - 1150 MHz P_{IN} = 5.6 W V_{CE} = 50V	35	---	---	W
G_p	f = 1025 - 1150 MHz P_{IN} = 5.6 W V_{CE} = 50V	9.0	---	---	dB

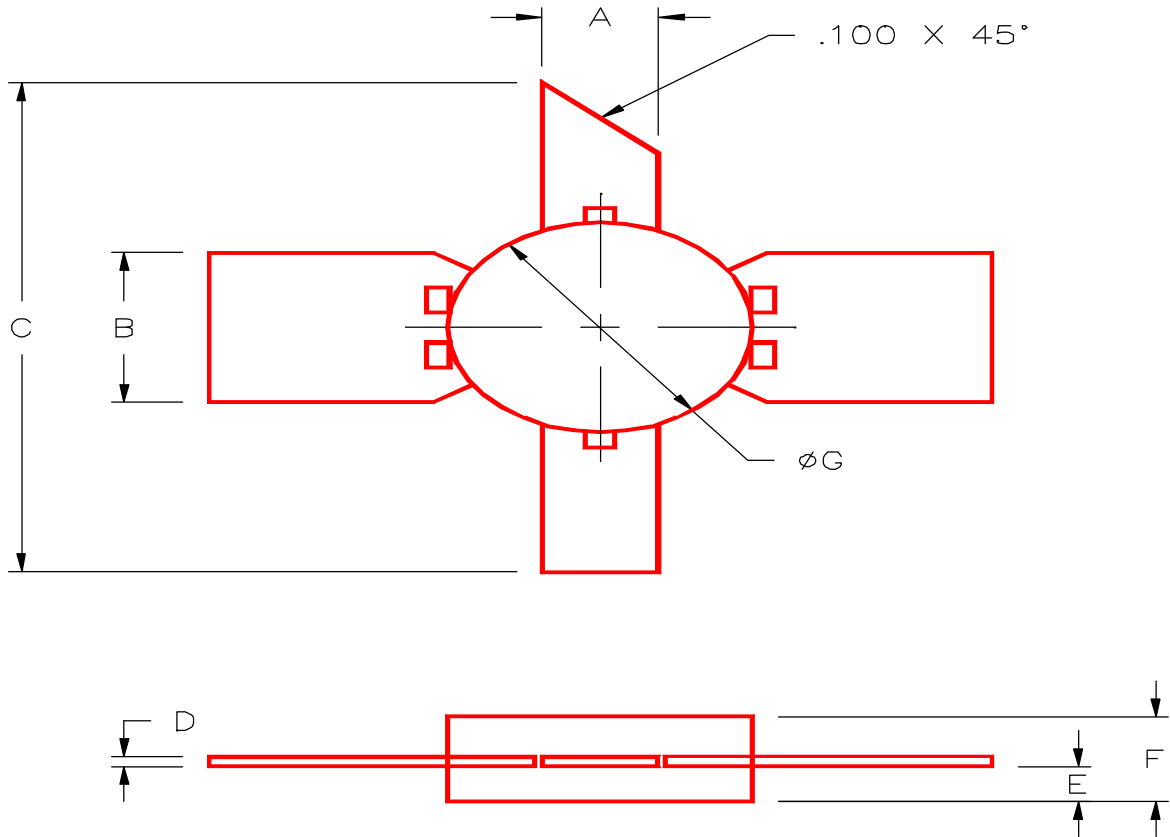
Conditions: Pulse Width = 10 μs Duty Cycle = 1%
IMPEDANCE DATA

FREQ	Z _{IN} (Ω)	Z _{CL} (Ω)
1025 MHz	2.7 + j9.1	16 - j5.8
1090 MHz	2.9 + j9.8	11 - j3.9
1150 MHz	2.8 + j11.7	11.4 - j4.7

MS2341

PACKAGE MECHANICAL DATA

PACKAGE STYLE M115



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.095/2,41	.105/2,67			
B	.195/4,95	.205/5,21			
C	1.000/25,40				
D	.004/0,10	.007/0,18			
E	.050/1,27	.065/1,65			
F	.120/3,05	.135/3,43			
G	.275/6,99	.285/7,21			